

Silicon PNP Power Transistors

2SB861

DESCRIPTION

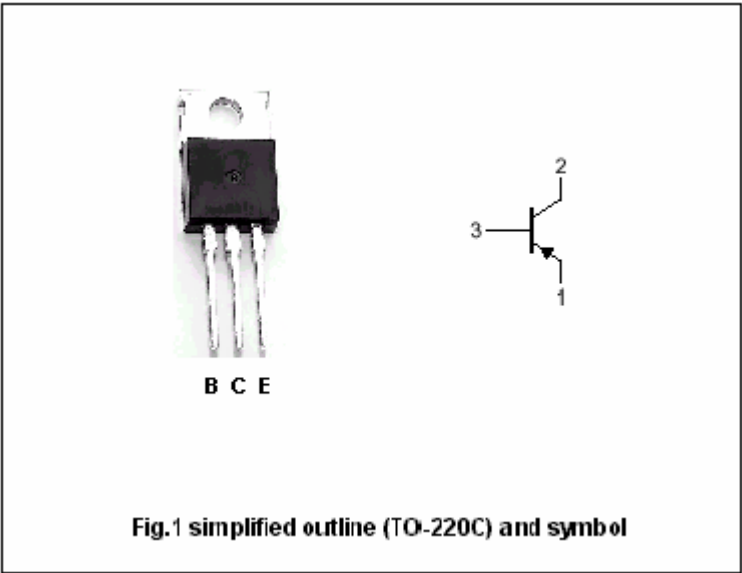
- With TO-220C package
- Complement to type 2SD1138

APPLICATIONS

- Low frequency power amplifier color TV vertical deflection output

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-200	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-2	A
I_{CP}	Collector current-Peak		-5	A
P_C	Collector power dissipation	$T_a=25$	1.8	W
		$T_C=25$	30	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-45~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50mA$; $R_{BE} = \infty$	-150			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	$I_E = -5mA$; $I_C = 0$	-6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -0.5A$; $I_B = -50mA$			-3.0	V
V_{BE}	Base-emitter voltage	$I_C = -50mA$; $V_{CE} = -4V$			-1.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -120V$; $I_E = 0$			-1	μA
h_{FE-1}	DC current gain	$I_C = -50mA$; $V_{CE} = -4V$	60		200	
h_{FE-2}	DC current gain	$I_C = -0.5A$; $V_{CE} = -10V$	60			
C_{OB}	Output capacitance	$I_E = 0$; $V_{CB} = -100V$, $f = 1MHz$		30		pF

◆ h_{FE-1} classifications

B	C
60-120	100-200

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Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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